
Please amend claims 7, 8, 12, 14, and 17 as follows:

1-5 (Cancelled).

6. (Previously amended) An interlevel dielectric structure comprising:

a single first dielectric layer situated on a semiconductor substrate, said single first dielectric layer having an upper surface;

a plurality of lines comprised of a conductive material extending along said upper surface of said single first dielectric layer; wherein:

each line of said plurality of lines has an upper surface, a lower surface, and at least one side surface;

adjacent lines of said plurality of lines have spaces situated therebetween;

the lower surfaces of each line of said plurality of lines is in contact with said upper surface of said single first dielectric layer; and

the upper surface of at least one line of said plurality of lines has thereon a layer of a refractory metal nitride;

a single second dielectric layer above both said plurality of lines and said single first dielectric layer, said single second dielectric layer having a lower surface in contact with the upper surface of each line of said plurality of lines; and

a single dielectric material situated in said space between adjacent lines of said plurality of lines, said single dielectric material not extending over the upper surface of each line of said plurality of lines, the upper surface of said single dielectric material being higher than the upper surface of each line of said plurality of lines, and the lower surface of said single dielectric material being lower than the lower surface of each line of said plurality of lines;

7. (Currently amended) The interlevel dielectric structure as defined in Claim 6, wherein:

said layer of refractory metal nitride has an electrical insulation spacer layer thereon, said electrical insulation layer having thereon said single second dielectric layer; and at least one side surface of the single dielectric material is in contact with at least one side surface of at least one of the plurality of lines.

8. (Currently amended) The interlevel dielectric structure as defined in Claim 7, wherein said electrical insulation spacer layer is a silicon dioxide layer.

9. (Original) The interlevel dielectric structure as defined in Claim 6, wherein said refractory metal nitride is titanium nitride.

10. (Previously amended) The interlevel dielectric structure as defined in Claim 6, wherein said single dielectric material comprises PTFE.

11. (Previously amended) The interlevel dielectric structure as defined in Claim 6, wherein at least one of the single first dielectric layer and single second dielectric layer comprises silicon dioxide.

12. (Currently amended) The interlevel dielectric structure as defined in Claim 6, wherein said conductive material is selected from the group consisting of polysilicon, aluminum, copper, tungsten, and ~~multiple layers of TiN/Al/TiN, TiN/Al/Ti, W/TiN/Ti,~~ or any combinations thereof.

13. (Previously amended) The interlevel dielectric structure as defined in Claim 6, where the single dielectric material has a dielectric constant of less than about 3.6.

14. (Currently amended) An interlevel dielectric structure comprising:

a first dielectric layer situated on a semiconductor substrate, said first dielectric layer having an upper surface;

a plurality of lines comprised of a conductive material extending along said upper surface of said first dielectric layer; wherein:

each line of said plurality of lines has an upper surface, a lower surface, and at least one side surface;

adjacent lines of said plurality of lines have spaces situated therebetween;

the lower surfaces of each line of said plurality of lines is in contact with said upper surface of said first dielectric layer;

the upper surface of at least one line of said plurality of lines has thereon a layer of titanium nitride;

said layer of titanium nitride has thereon a silicon dioxide spacer layer;

said silicon dioxide layer not being in contact with at least one side surface of at least one of the plurality of lines;

a second dielectric layer above both said plurality of lines and said first dielectric layer, said second dielectric layer having a lower surface in contact with the silicon dioxide layer of each line of said plurality of lines; and

a dielectric material, having at least one side surface, situated in said space between adjacent lines of said plurality of lines, said dielectric material not extending over the upper surface of each line of said plurality of lines, the upper surface of said dielectric material

said dielectric material being lower than the lower surface of each line of said plurality of

lines, and at least one side surface of the dielectric material being in contact with at least one side surface of at least one of the plurality of lines.

15. (Original) The interlevel dielectric structure as defined in Claim 14, wherein said dielectric material comprises PTFE.

16. (Original) The interlevel dielectric structure as defined in Claim 14, wherein at least one of the first and second dielectric layers comprises silicon dioxide.

17. (Currently amended) The interlevel dielectric structure as defined in Claim 14, wherein said conductive material is selected from the group consisting of polysilicon, aluminum, copper, tungsten, and ~~multiple layers of TiN/Al/TiN, TiN/Al/Ti, W/TiN/Ti,~~ or any combinations thereof.

18. (Original) The interlevel dielectric structure as defined in Claim 14, where the dielectric material has a dielectric constant of less than about 3.6.